

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 61-081657

(43)Date of publication of application : 25.04.1986

(51)Int.Cl.

H01L 21/88
H01L 21/94

(21)Application number : 59-204732

(71)Applicant : SANYO ELECTRIC CO LTD

(22)Date of filing : 28.09.1984

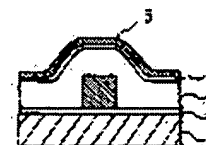
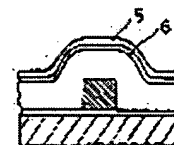
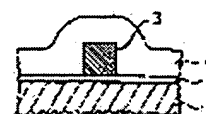
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To prevent uneven deformation of wiring on a protection film by providing a protection film consisting of a material having a higher melting point than that of interlayer insulation film between said interlayer insulation film and wiring arranged thereon.

CONSTITUTION: A semiconductor substrate 1, an insulation film 2, a lower wiring 3 and an interlayer insulating film 4 are sequentially formed. A protecting film 6 consisting of SiO₂ not including impurity such as phosphorus is deposited by the CVD method in the thickness of about 0.05 μ m on the interlayer insulation film consisting of phosphor glass under the reflow condition at about 1,000°C. An upper layer wiring 5 in the thickness of 0.1 μ m consisting of polysilicon is formed by reduced pressure CVD method on the protection film 6. Thereafter, the upper wiring 5 is annealed for 10min at 1,000°C under the nitrogen ambient. In this case, since SiO₂ of protection film 6 is not dissolved up to a temperature of 1,700°C, rigidity can be kept and the upper wiring 5 does not show uneven deformation.



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